

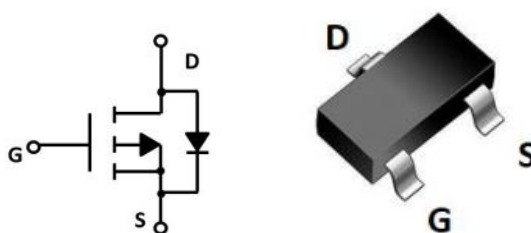


安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO. , LTD.

FS3409M

SOT-23 -30V P Channel Enhancement 沟道增强型 MOS Field Effect Transistor 场效应管



■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	-30	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	± 20	V
Drain Current (continuous)漏极电流-连续	I_D (at $T_A = 25^\circ C$)	-2.6	A
Drain Current (pulsed)漏极电流-脉冲	I_{DM}	-15	A
Total Device Dissipation 总耗散功率	P_D (at $T_A = 25^\circ C$)	1000	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	125	$^\circ C/W$
Junction/Storage Temperature 结温/储存温度	T_J, T_{stg}	-55~150	$^\circ C$

■ Device Marking 产品字标

FS3409M=S3



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■Electrical Characteristics 电特性

(T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压(I _D = -250uA, V _{GS} =0V)	BV _{DSS}	-30	—	—	V
Gate Threshold Voltage 栅极开启电压(I _D = -250uA, V _{GS} = V _{DS})	V _{GS(th)}	-1.4	-1.9	-2.4	V
Zero Gate Voltage Drain Current 零栅压漏极电流(V _{GS} =0V, V _{DS} = -30V)	I _{DSS}	—	—	1	uA
Gate Body Leakage 栅极漏电流(V _{GS} =±20V, V _{DS} =0V)	I _{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance 静态漏源导通电阻(I _D = -2.6A, V _{GS} = -10V) (I _D = -2A, V _{GS} = -4.5V)	R _{DS(ON)}	—	77 125	110 180	mΩ
Diode Forward Voltage Drop 内附二极管正向压降(I _{SD} = -1A, V _{GS} =0V)	V _{SD}	—	—	-1	V
Input Capacitance 输入电容 (V _{GS} =0V, V _{DS} = -15V, f=1MHz)	C _{ISS}	—	200	—	pF
Common Source Output Capacitance 共源输出电容(V _{GS} =0V, V _{DS} = -15V, f=1MHz)	C _{OSS}	—	45	—	pF
Reverse Transfer Capacitance 反馈电容(V _{GS} =0V, V _{DS} = -15V, f=1MHz)	C _{RSS}	—	30	—	pF
Total Gate Charge 栅极电荷密度 (V _{DS} = -15V, I _D = -2.6A, V _{GS} = -10V)	Q _g	—	4	—	nC
Gate Source Charge 栅源电荷密度 (V _{DS} = -15V, I _D = -2.6A, V _{GS} = -10V)	Q _{gs}	—	1	—	nC
Gate Drain Charge 栅漏电荷密度 (V _{DS} = -15V, I _D = -2.6A, V _{GS} = -10V)	Q _{gd}	—	1	—	nC
Turn-ON Delay Time 开启延迟时间 (V _{DS} = -15V I _D = -1A, R _{GEN} =3Ω, V _{GS} = -10V)	t _{d(on)}	—	8	—	ns
Turn-ON Rise Time 开启上升时间 (V _{DS} = -15V I _D = -1A, R _{GEN} =3Ω, V _{GS} = -10V)	t _r	—	4	—	ns
Turn-OFF Delay Time 关断延迟时间 (V _{DS} = -15V I _D = -1A, R _{GEN} =3Ω, V _{GS} = -10V)	t _{d(off)}	—	12	—	ns
Turn-OFF Fall Time 关断下降时间 (V _{DS} = -15V I _D = -1A, R _{GEN} =3Ω, V _{GS} = -10V)	t _f	—	4	—	ns

■ Typical Characteristic Curve 典型特性曲线

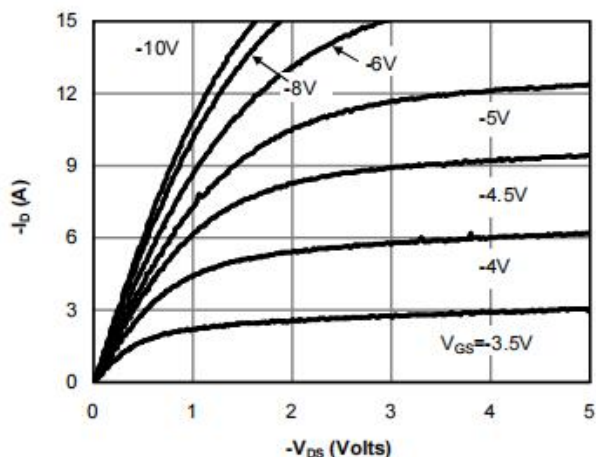


Figure 1: Output Characteristics

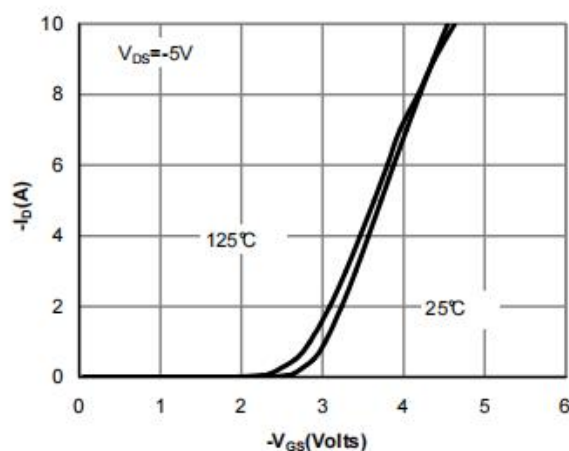


Figure 2: Transfer Characteristics

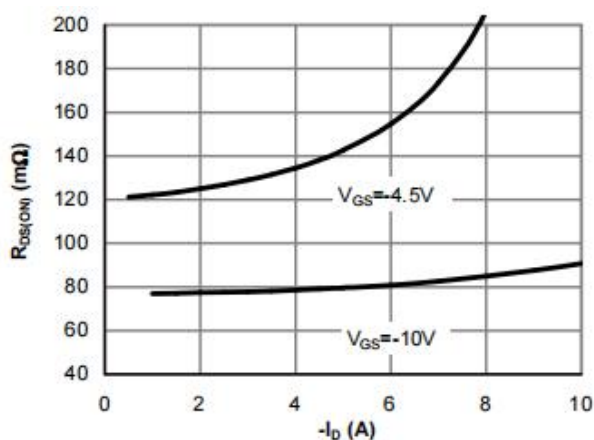


Figure 3: On-Resistance vs. Drain Current

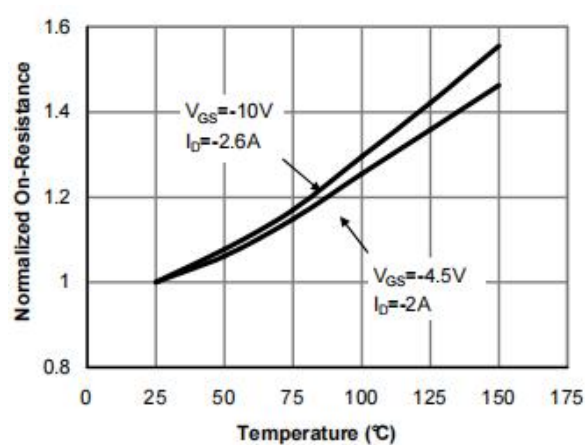


Figure 4: On-Resistance vs. Temperature

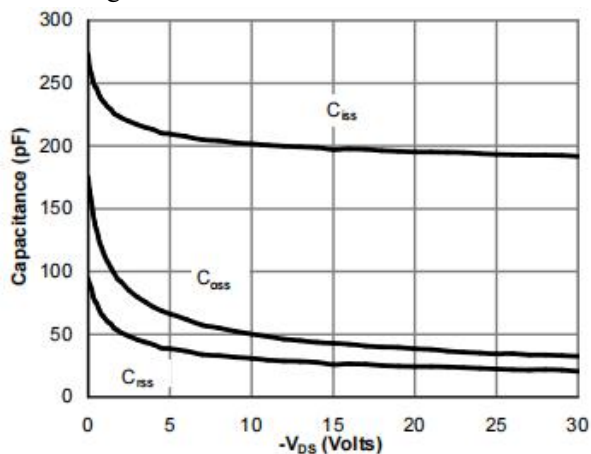


Figure 5: Capacitance Characteristics

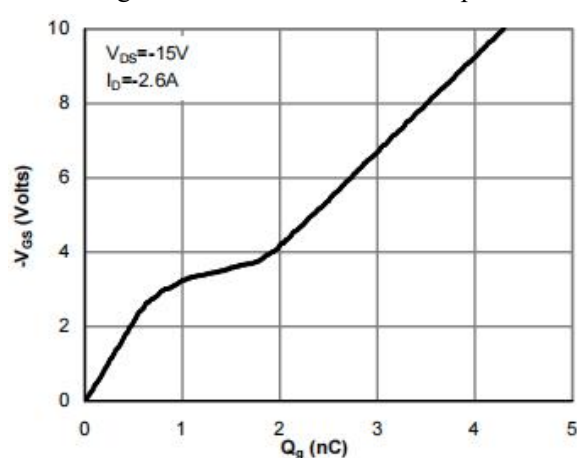


Figure 6: Gate-Charge Characteristics

■ Typical Characteristic Curve 典型特性曲线

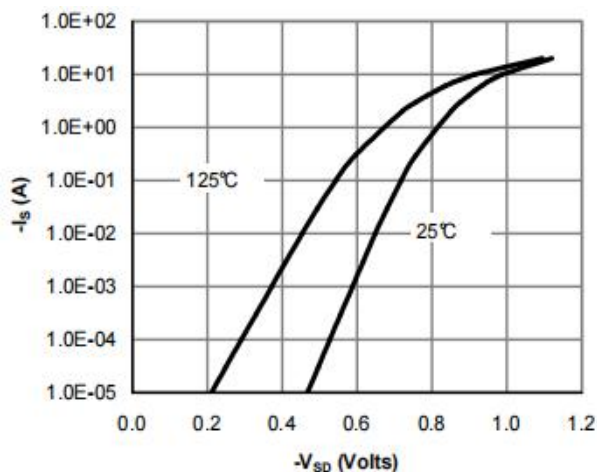


Figure 7: Diode Characteristics

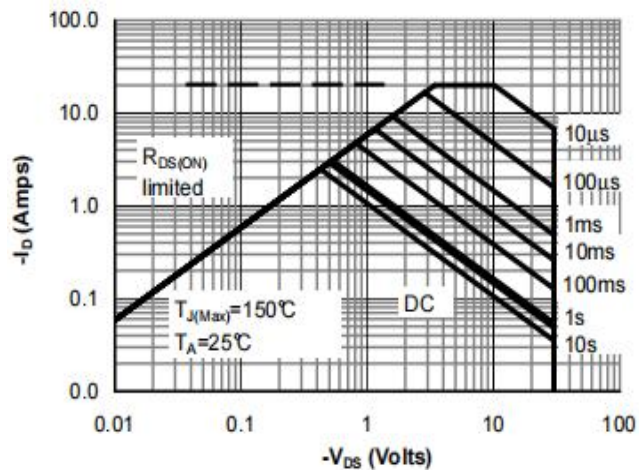


Figure 8: Safe Operating Area

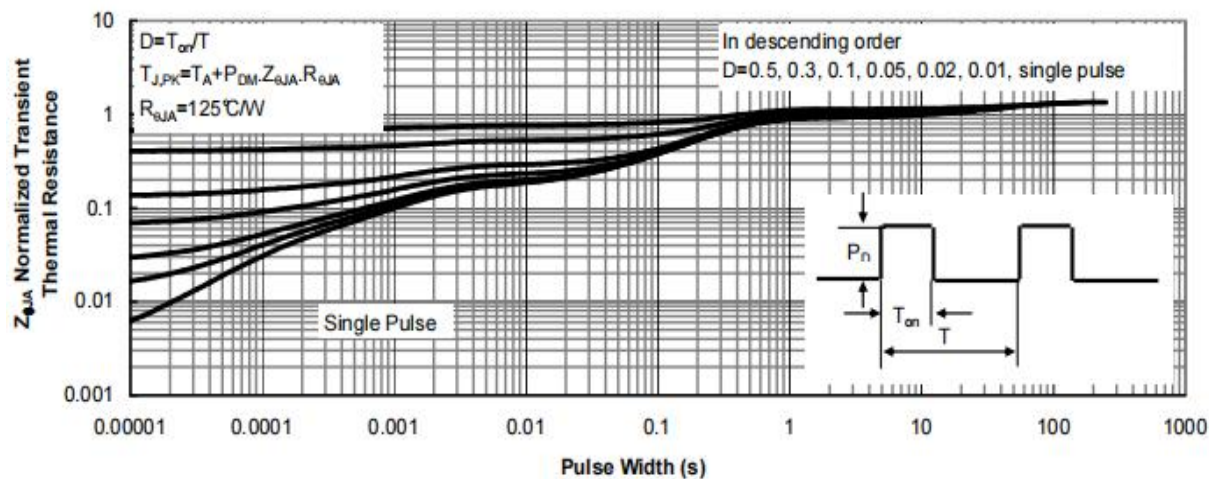
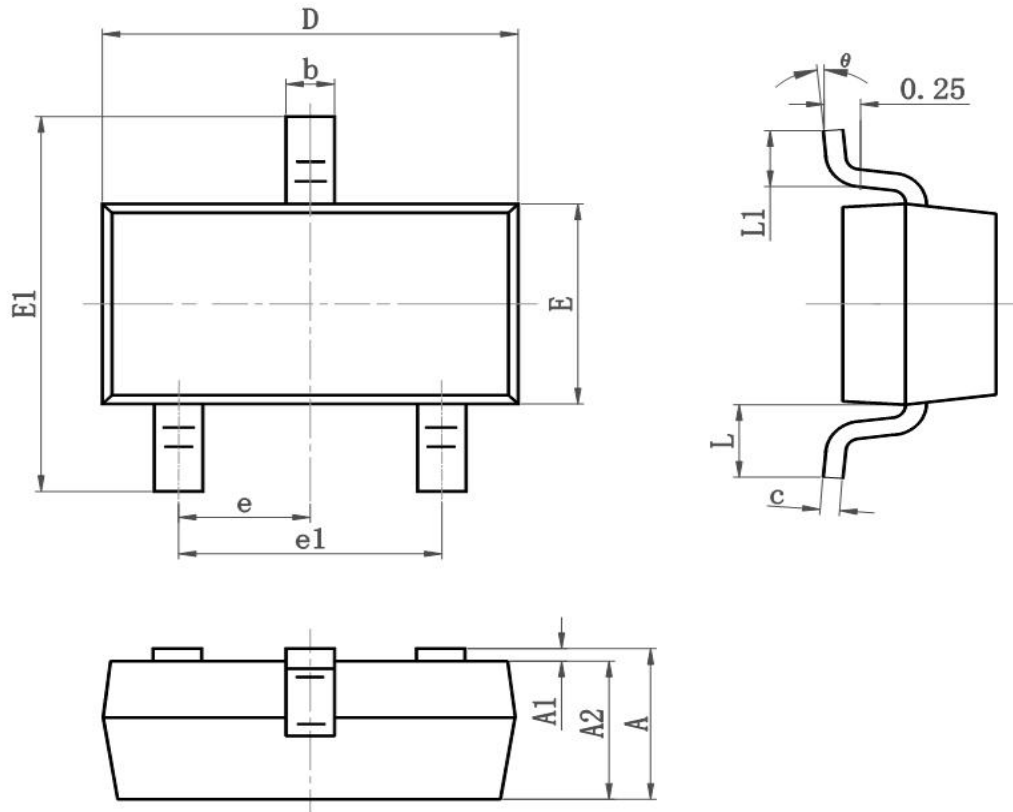


Figure 9: Transient Thermal Response Curve

■ Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.050	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°